

GL359

PNP SILICON PLANAR HIGH CURRENT TRANSISTOR

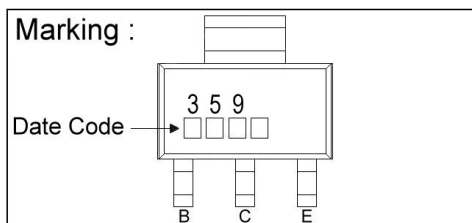
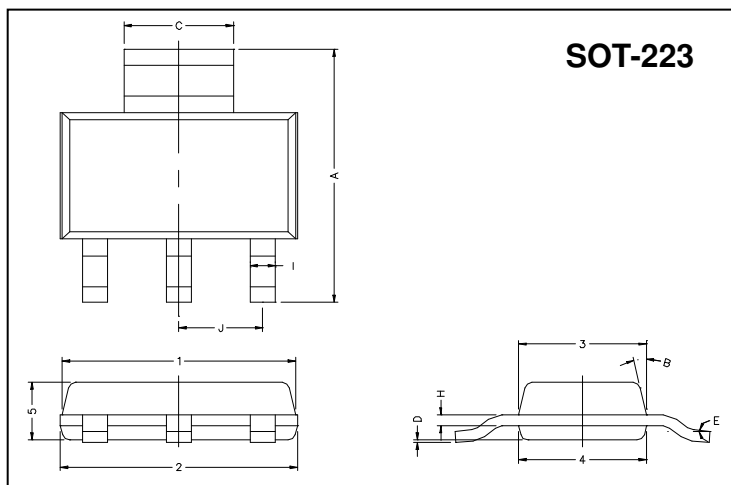
Description

The GL359 is designed for general purpose switching and amplifier applications.

Features

- 5 Amps continuous current, up to 10Amps peak current
- Excellent gain characteristic specified up to 10Amps
- Very low saturation voltages

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	-140	V
Collector to Emitter Voltage	VCEO	-100	V
Emitter to Base Voltage	VEBO	-6	V
Collector Current (DC)	Ic	-5	A
Collector Current (Pulse)	Ic	-10	A
Total Power Dissipation	PD	3	W

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 4 square inch minimum.

Electrical Characteristics (Ta = 25°C, unless otherwise stated)

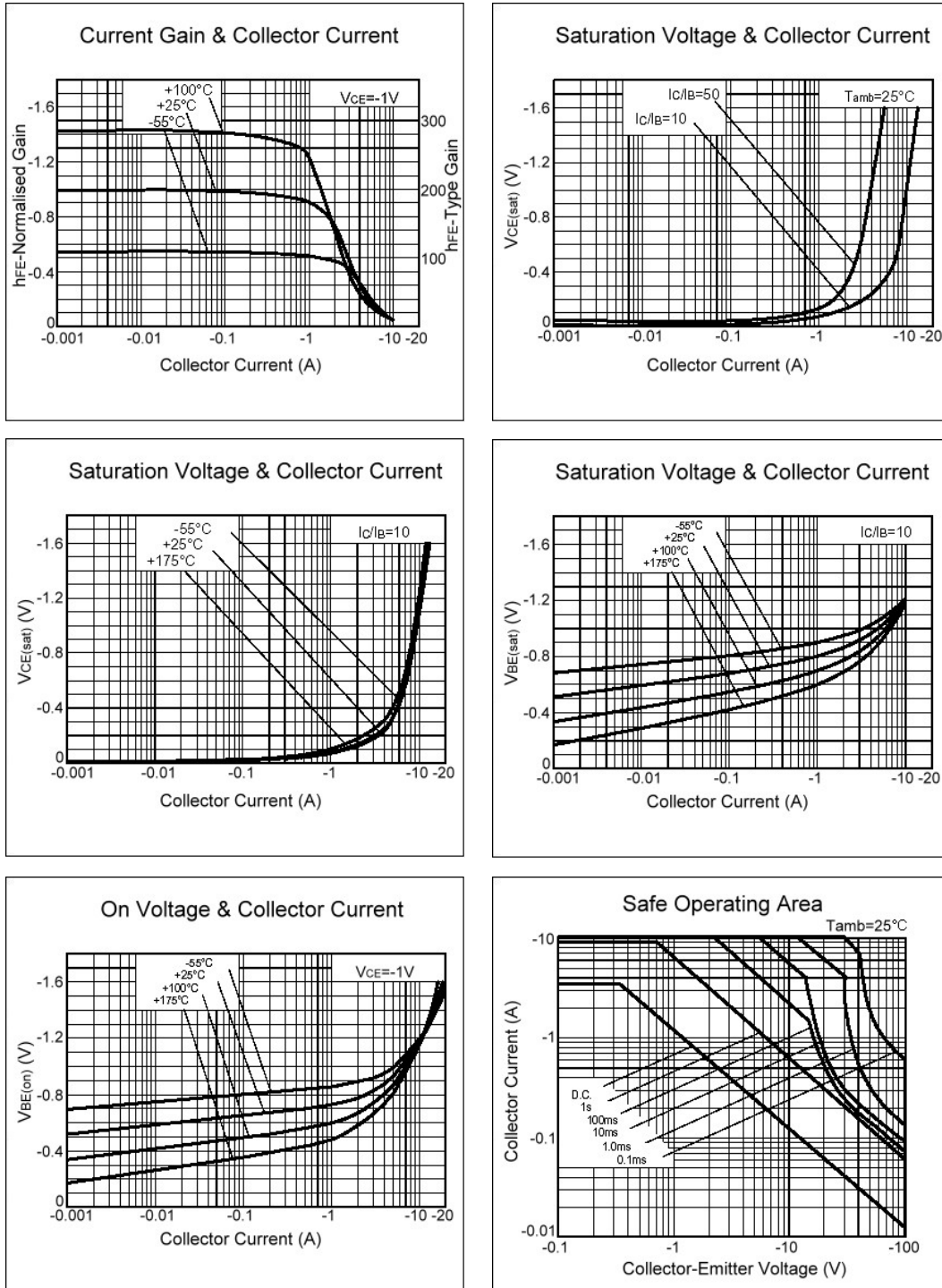
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-140	-	-	V	IC=-100uA, IE=0
*BVCEO	-100	-	-	V	IC=-10mA, IB=0
BVEBO	-6	-	-	V	IE=-100uA, IC=0
ICBO	-	-	-50	nA	VCB=-100V, IE=0
ICES	-	-	-50	nA	VCE=-100V
IEBO	-	-	-10	nA	VEB=-6V, IC=0
*VCE(sat)1	-	-20	-50	mV	IC=-100mA, IB=-10mA
*VCE(sat)2	-	-90	-115	mV	IC=-1A, IB=-100mA
*VCE(sat)3	-	-160	-220	mV	IC=-2A, IB=-200mA
*VCE(sat)4	-	-300	-420	mV	IC=-4A, IB=-400mA
*VBE(sat)	-	-1.01	-1.17	V	IC=-4A, IB=-400mA
*VBE(on)	-	-0.925	-1.16	V	VCE=-1V, IC=-4A
*hFE1	100	200			VCE=-1V, IC=-10mA
*hFE2	100	200	300		VCE=-1V, IC=-1A
*hFE3	50	90			VCE=-1V, IC=-3A
*hFE4	30	50			VCE=-1V, IC=-4A
*hFE5	-	15			VCE=-1V, IC=-10A
fT	-	125	-	MHz	VCE=-10V, IC=-100mA, f=50MHz

Cob	-	65	-	pF	V _{CB} =-10V, I _E =0, f=1MHz
t _{on}	-	110	-	ns	V _{CC} =-10V, I _C =-2A, I _{B1} =-200mA, I _{B2} =200mA
t _{off}	-	460	-		

*Measured under pulse condition. Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Spice parameter data is available upon request for this device.

Characteristics Curve



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